Silicon Carbide Micro-/Nanosystems for Sensing and Energy Applications

Dec. 6, 2013 | 2 p.m. | DeWalt Seminar Room, 2164 Martin Hall

**ABSTRACT:** Silicon carbide (SiC), a wide bandgap semiconductor, is emerging as a material to address the limitations of silicon as it is temperature tolerant, radiation resistant, and chemically inert. In this talk, Maboudian will present recent advances in the materials science and manufacturing technology of SiC thin film and low dimensional structures. This includes deposition, metallization, and fabrication of semiconductor microdevices, with particular emphasis on sensor and energy technologies.

**BIO:** Roya Maboudian is professor of chemical and biomolecular engineering, associate director of the Center of Integrated Nanomechanical Systems (COINS), and faculty affiliate of the Berkeley Sensor & Actuator Center (BSAC) at the University of California, Berkeley. She received her B.S. degree in Electrical Engineering from the Catholic University of America, Washington, D.C., and her M.S. and Ph.D. degrees in Applied Physics from the California Institute of Technology in Pasadena.

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